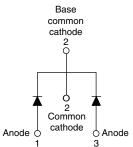


Vishay Semiconductors

# Ultrafast Rectifier, 2 x 10 A FRED Pt®







PRODUCT SUMMARY						
Package	TO-220AB					
I <sub>F(AV)</sub>	2 x 10 A					
$V_{R}$	200 V					
V <sub>F</sub> at I <sub>F</sub>	See Electrical table					
t <sub>rr</sub> typ.	See Recovery table					
T <sub>J</sub> max.	175 °C					
Diode variation	Common cathode					

#### **FEATURES**

- · Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)





## RoHS

HALOGEN
FREE
Available

### **DESCRIPTION/APPLICATIONS**

VS-MUR2020CTPbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Peak repetitive reverse voltage		$V_{RRM}$		200	V		
Average rectified forward current	per leg	I <sub>F(AV)</sub>		10	^		
	total device		Rated V <sub>R</sub> , T <sub>C</sub> = 145 °C	20			
Non-repetitive peak surge current per leg		I <sub>FSM</sub>		100	Α		
Peak repetitive forward current per leg		I <sub>FM</sub>	Rated V <sub>R</sub> , square wave, 20 kHz, T <sub>C</sub> = 145 °C	20			
Operating junction and storage temperatures		T <sub>J</sub> , T <sub>Stg</sub>		- 65 to 175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	TEST CONDITIONS MIN.			UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	200	-	-			
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 8 A, T <sub>J</sub> = 125 °C	-	-	0.85	V		
		I <sub>F</sub> = 16 A	-	-	1.15			
		I <sub>F</sub> = 16 A, T <sub>J</sub> = 125 °C	-	-	1.05			
Reverse leakage current	lookaga aurrant	$V_R = V_R$ rated	-	-	15			
neverse leakage current	I <sub>R</sub>	$T_J = 150 ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	-	250	μΑ		
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	55	-	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH		



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, dI_F/dt =$	$50 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	1	-	35		
Reverse recovery time		I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1.0 A, I <sub>REC</sub> = 0.25 A		-	-	25		
	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	$I_F = 10 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 160 \text{ V}$	-	21	-	ns -	
		T <sub>J</sub> = 125 °C		-	35	-		
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	1.9	-	- A	
		T <sub>J</sub> = 125 °C		-	4.8	-		
Reverse recovery charge	0	T <sub>J</sub> = 25 °C		-	25	-	200	
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	78	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 65	-	175	°C	
Thermal resistance, per leg	В		-	-	2.5		
junction to case total device	R <sub>thJC</sub>		-	-	1.25		
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>		-	-	50	°C/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-		
Maint			-	2.0	-	g	
Weight			-	0.07	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AB		MUR2020CT			

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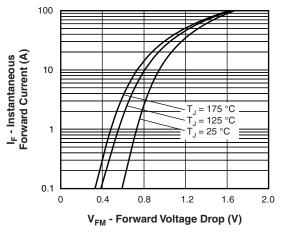


Fig. 1 - Maximum Forward Voltage Drop Characteristics

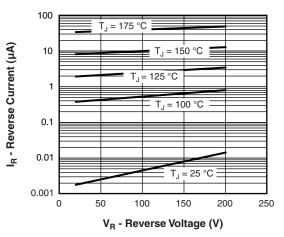


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

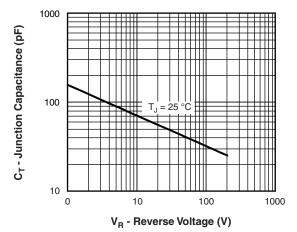


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

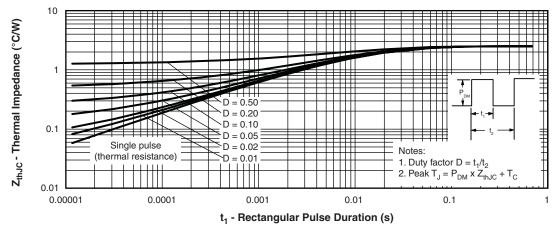
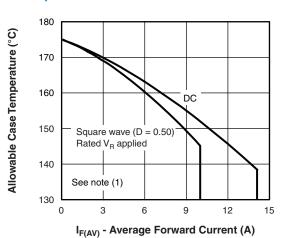


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

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Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

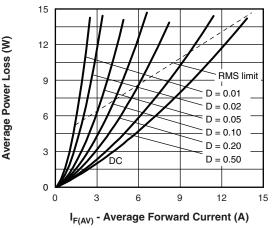


Fig. 6 - Forward Power Loss Characteristics

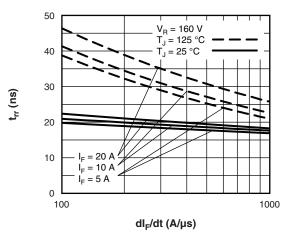


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

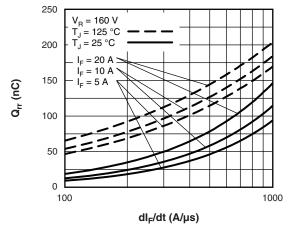


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $^{(1)}$  Formula used:  $T_{C} = T_{J}$  - (Pd + Pd\_{REV}) x  $R_{thJC};$  $Pd = Forward\ power\ loss = I_{F(AV)}\ x\ V_{FM}\ at\ (I_{F(AV)}/D)\ (see\ fig.\ 6);$   $Pd_{REV} = Inverse\ power\ loss = V_{R1}\ x\ I_R\ (1\ -\ D);\ I_R\ at\ V_{R1} = Rated\ V_R$ 

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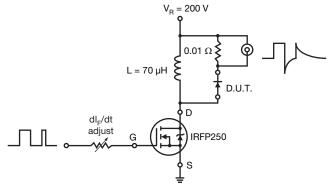
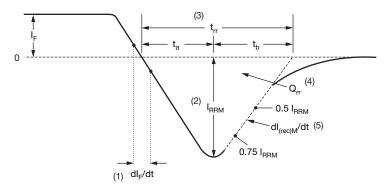


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RBM</sub> and 0.50 I<sub>RBM</sub> extrapolated to zero current.
- (4)  ${\rm Q_{rr}}$  area under curve defined by  ${\rm t_{rr}}$  and  ${\rm I_{BBM}}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

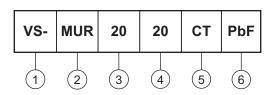
(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 10 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Ultrafast MUR series

Current rating (20 = 20 A)

4 - Voltage rating (20 = 200 V)

5 - CT = Center tap (dual)

6 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTIO							
VS-MUR2020CTPbF	50	1000	Antistatic plastic tube				
VS-MUR2020CT-N3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions		www.vishay.com/doc?95222			
Part marking information	TO-220ABPbF	www.vishay.com/doc?95225			
	TO-220AB-N3	www.vishay.com/doc?95028			
SPICE model		www.vishay.com/doc?95272			



## Vishay Semiconductors

## **TO-220AB**

#### **DIMENSIONS** in millimeters and inches



## Lead assignments

### **Diodes**

- 1. Anode/open
- 2. Cathode
- 3. Anode

#### Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIM	IETERS	INCHES		NOTES	
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
E	10.11	10.51	0.398	0.414	3, 6	
E1	6.86	8.89	0.270	0.350	6	
E2	-	0.76	-	0.030	7	
е	2.41	2.67	0.095	0.105		
e1	4.88	5.28	0.192	0.208		
H1	6.09	6.48	0.240	0.255	6, 7	
L	13.52	14.02	0.532	0.552		
L1	3.32	3.82	0.131	0.150	2	
ØΡ	3.54	3.73	0.139	0.147		
Q	2.60	3.00	0.102	0.118		
θ	90° t	o 93°	90° to 93°			
		•	•	•		

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip



## **Legal Disclaimer Notice**

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